NTE ELECTRONICS, INC.

NTE399
Silicon NPN Transistor
High Voltage Video Amp
(Compl to NTE2366)

Absolute Maximum Ratings:

Collector–Base Voltage, V_{CBO} 300V

Collector–Emitter Voltage, V_{CEO} 300V

Emitter–Base Voltage, V_{EBO} 6V

Collector Current, I_C

Continuous 100mA

Peak 300mA

Collector Power Dissipation, P_C 900mW

Operating Junction Temperature, T_J . . . . . +150°C

Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 200V, I_E = 0	–	–	1.0	µA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 6V, I_C = 0	–	–	1.0	µA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 5mA	100	–	220	
Current Gain–Bandwidth Product	f_T	V_{CB} = 30V, I_C = 10mA	50	–	–	MHz
Output Capacitance	C_{ob}	V_{CB} = 10V, f = 1MHz	–	–	7.5	pF
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 20mA, I_B = 2mA	–	–	0.6	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 20mA, I_B = 2mA	–	–	1.0	V